First-principle high-throughput calculations of carrier effective masses of two-dimensional transition metal dichalcogenides*

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Supporting Information

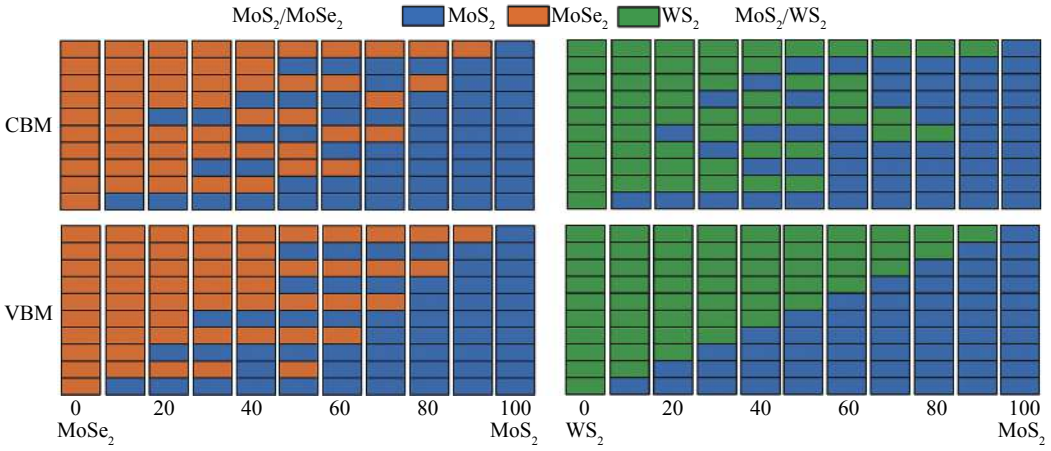

Fig. S1. (Color online) The scheme of the stacking orders for each structures with the lowest m^*_{in} for CBMs and VBMs in $MoS_2/MoSe_2$ and MoS_2/WS_2 heterostructures.

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